

FQPF30N06L

N-Channel QFET® MOSFET

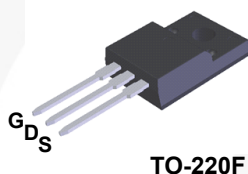
60 V, 22.5 A, 35 mΩ

Description

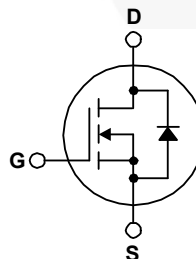
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 22.5 A, 60 V, $R_{DS(on)} = 35 \text{ m}\Omega$ (Max.) @ $V_{GS}=10 \text{ V}$, $I_D = 11.3 \text{ A}$
- Low Gate Charge (Typ. 15 nC)
- Low C_{rss} (Typ. 50 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



TO-220F



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQPF30N06L	Unit
V_{DSS}	Drain-Source Voltage	60	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	22.5	A
	- Continuous ($T_C = 100^\circ\text{C}$)	15.9	A
I_{DM}	Drain Current - Pulsed (Note 1)	90	A
V_{GSS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	350	mJ
I_{AR}	Avalanche Current (Note 1)	22.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	3.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	38	W
	- Derate above 25°C	0.25	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQPF30N06L	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.9	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF30N06L	FQPF30N06L	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics T_c = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	60	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.06	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 48 V, T _C = 150°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V	--	--	-100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1.0	--	2.5	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 11.3 A	--	0.027	0.035	Ω
		V _{GS} = 5 V, I _D = 11.3 A	--	0.035	0.045	Ω
g _{FS}	Forward Transconductance	V _{DS} = 25 V, I _D = 11.3 A	--	22	--	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	800	1040	pF
C _{oss}	Output Capacitance		--	270	350	pF
C _{rss}	Reverse Transfer Capacitance		--	50	65	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 30 V, I _D = 16 A, R _G = 25 Ω (Note 4)	--	15	40	ns
t _r	Turn-On Rise Time		--	210	430	ns
t _{d(off)}	Turn-Off Delay Time		--	60	130	ns
t _f	Turn-Off Fall Time		--	110	230	ns
Q _g	Total Gate Charge	V _{DS} = 48 V, I _D = 32 A, V _{GS} = 5 V (Note 4)	--	15	20	nC
Q _{gs}	Gate-Source Charge		--	3.5	--	nC
Q _{gd}	Gate-Drain Charge		--	8.5	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current	--	--	22.5	A	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	90	A	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 22.5 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 32 A,	--	60	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs	--	90	--	nC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 810 μH, I_{AS} = 22.5 A, V_{DD} = 25 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 32 A, di/dt ≤ 300 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Characteristics

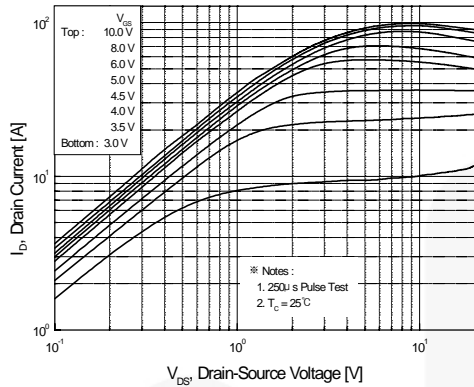


Figure 1. On-Region Characteristics

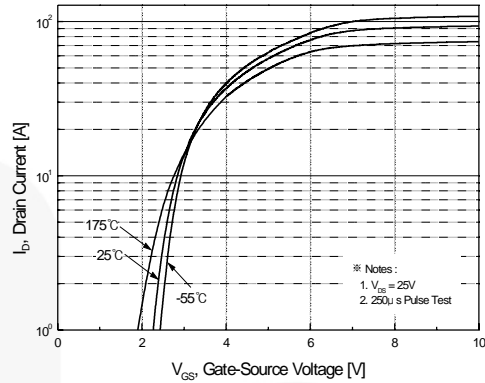


Figure 2. Transfer Characteristics

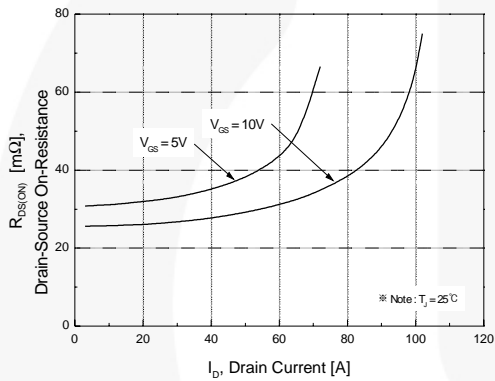


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

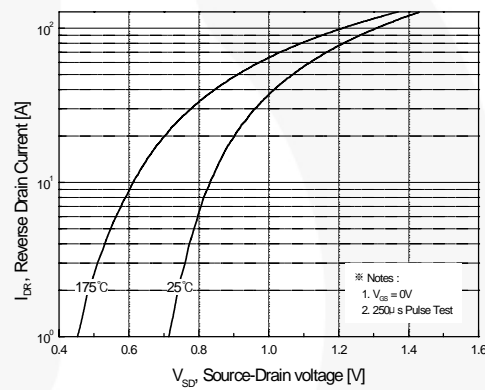


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

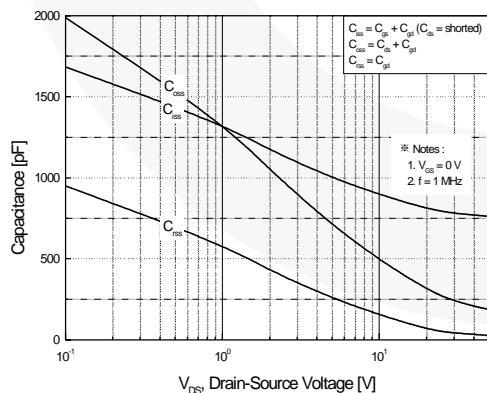


Figure 5. Capacitance Characteristics

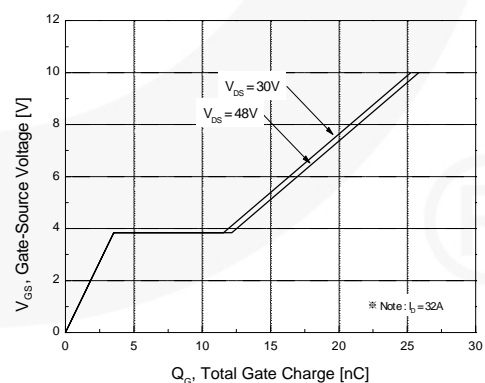


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

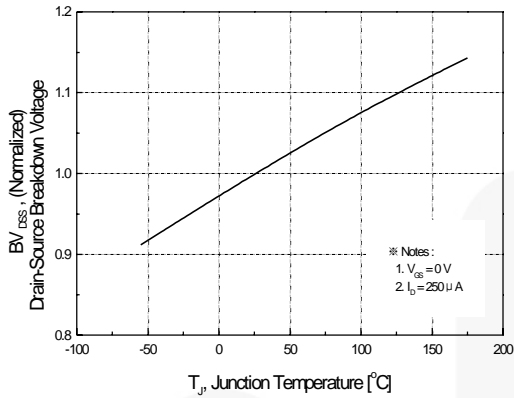


Figure 7. Breakdown Voltage Variation vs. Temperature

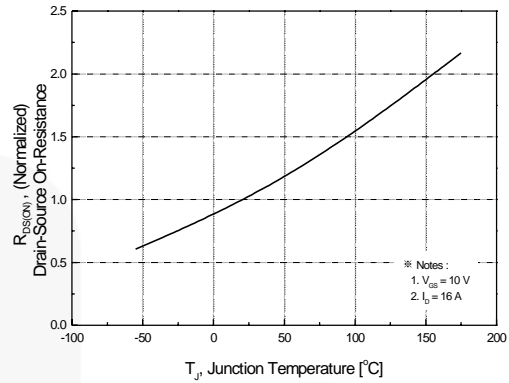


Figure 8. On-Resistance Variation vs. Temperature

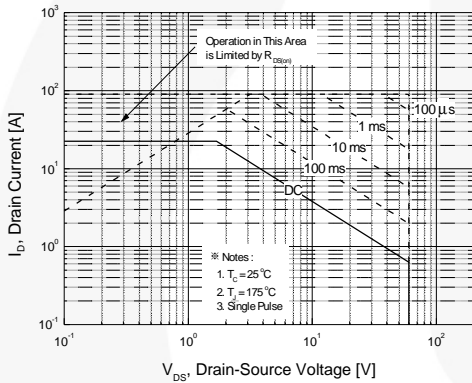


Figure 9. Maximum Safe Operating Area

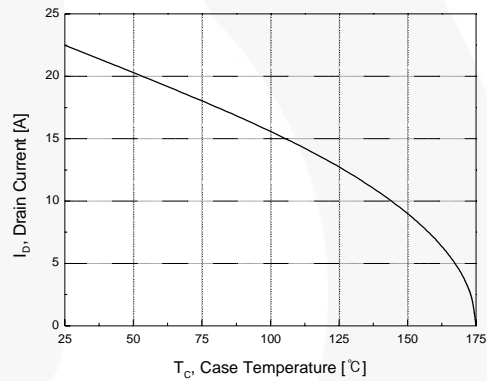


Figure 10. Maximum Drain Current vs. Case Temperature

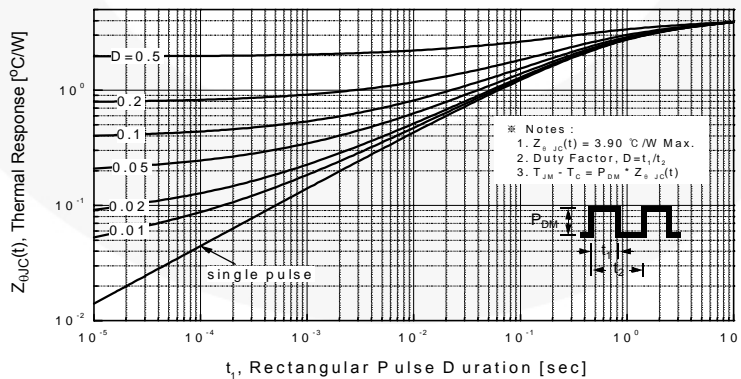


Figure 11. Transient Thermal Response Curve

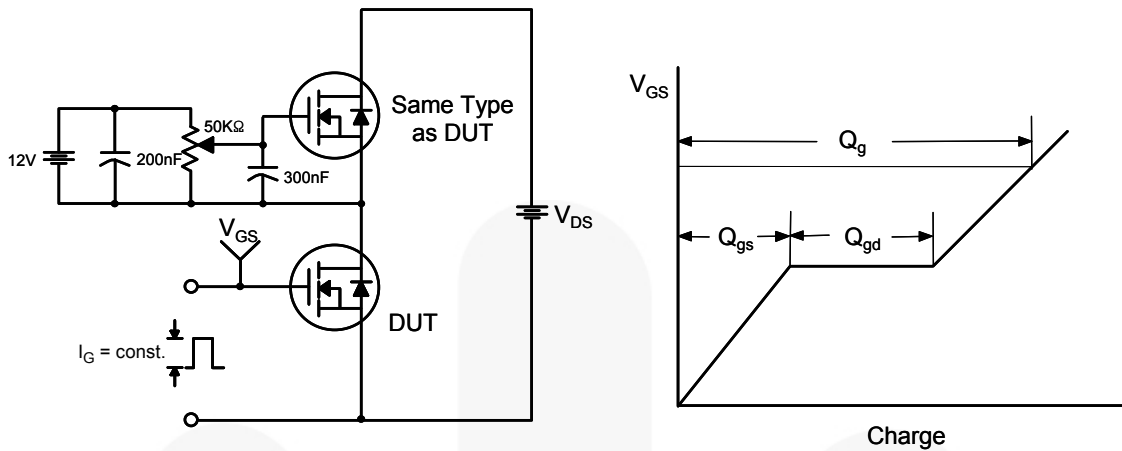


Figure 12. Gate Charge Test Circuit & Waveform

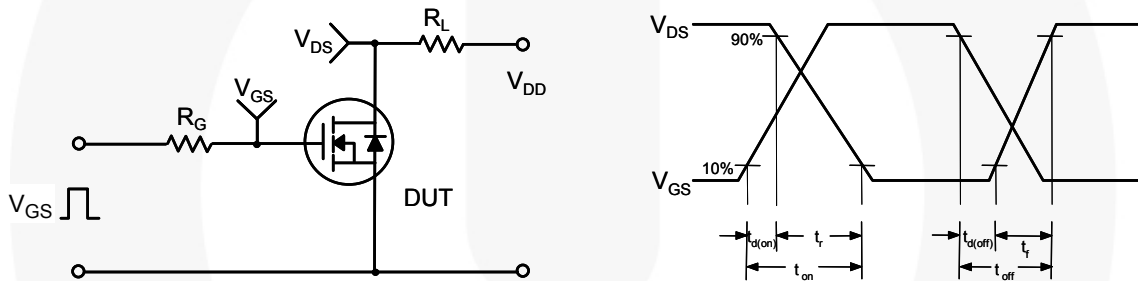


Figure 13. Resistive Switching Test Circuit & Waveforms

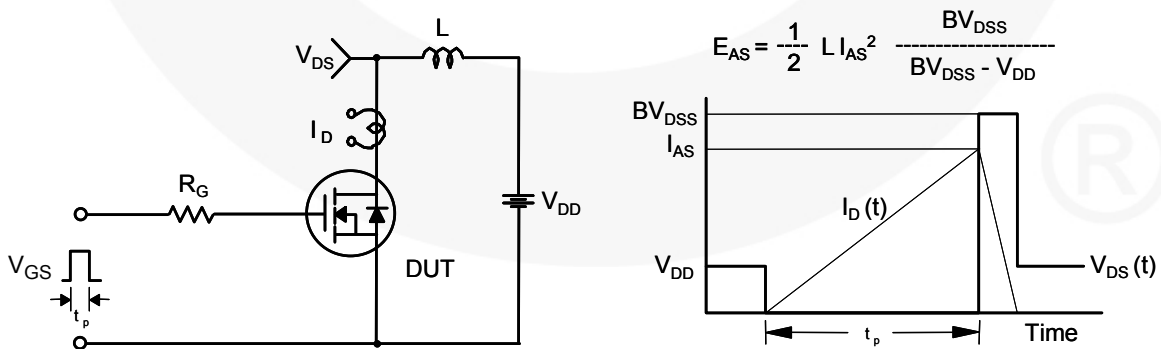


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

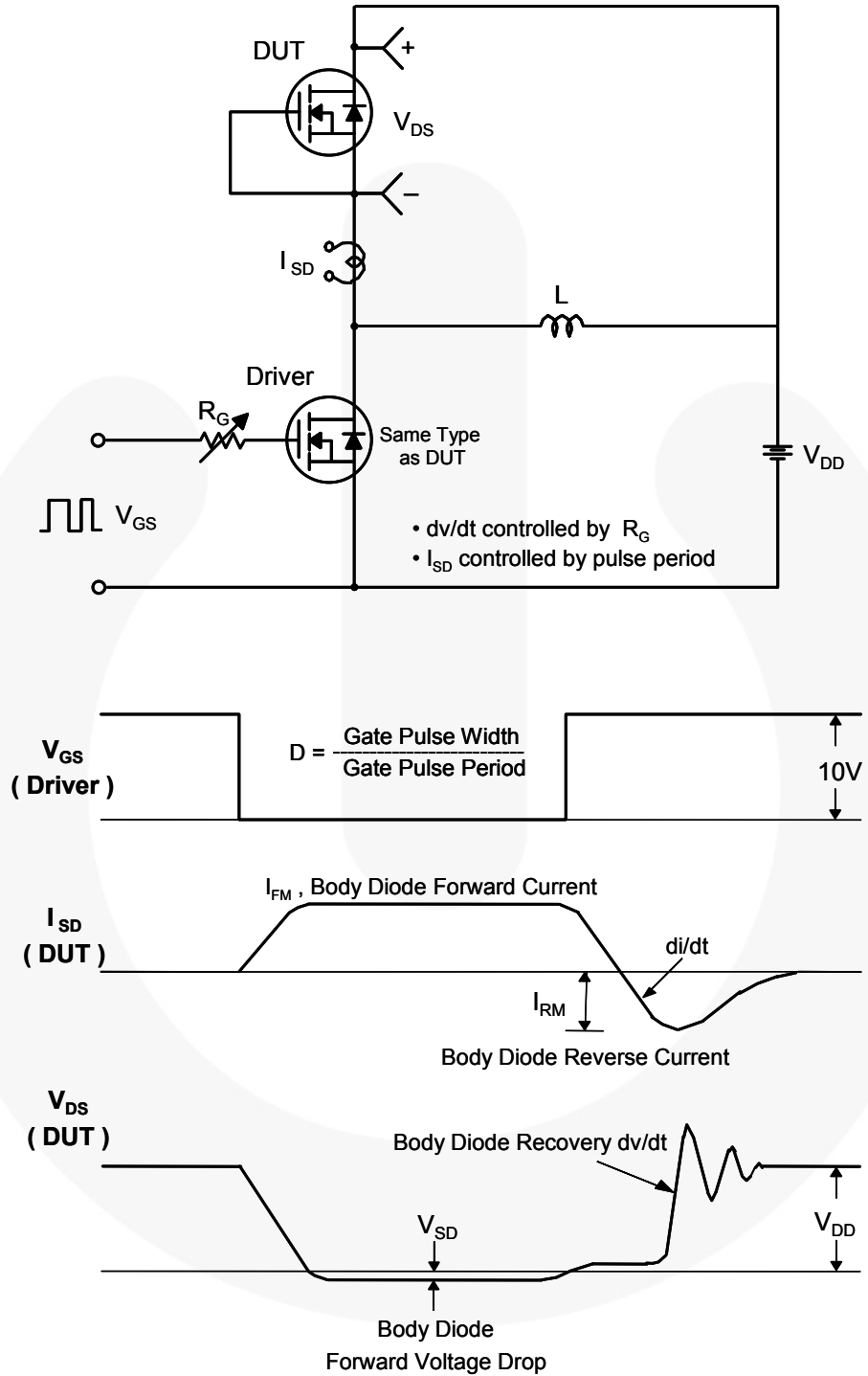
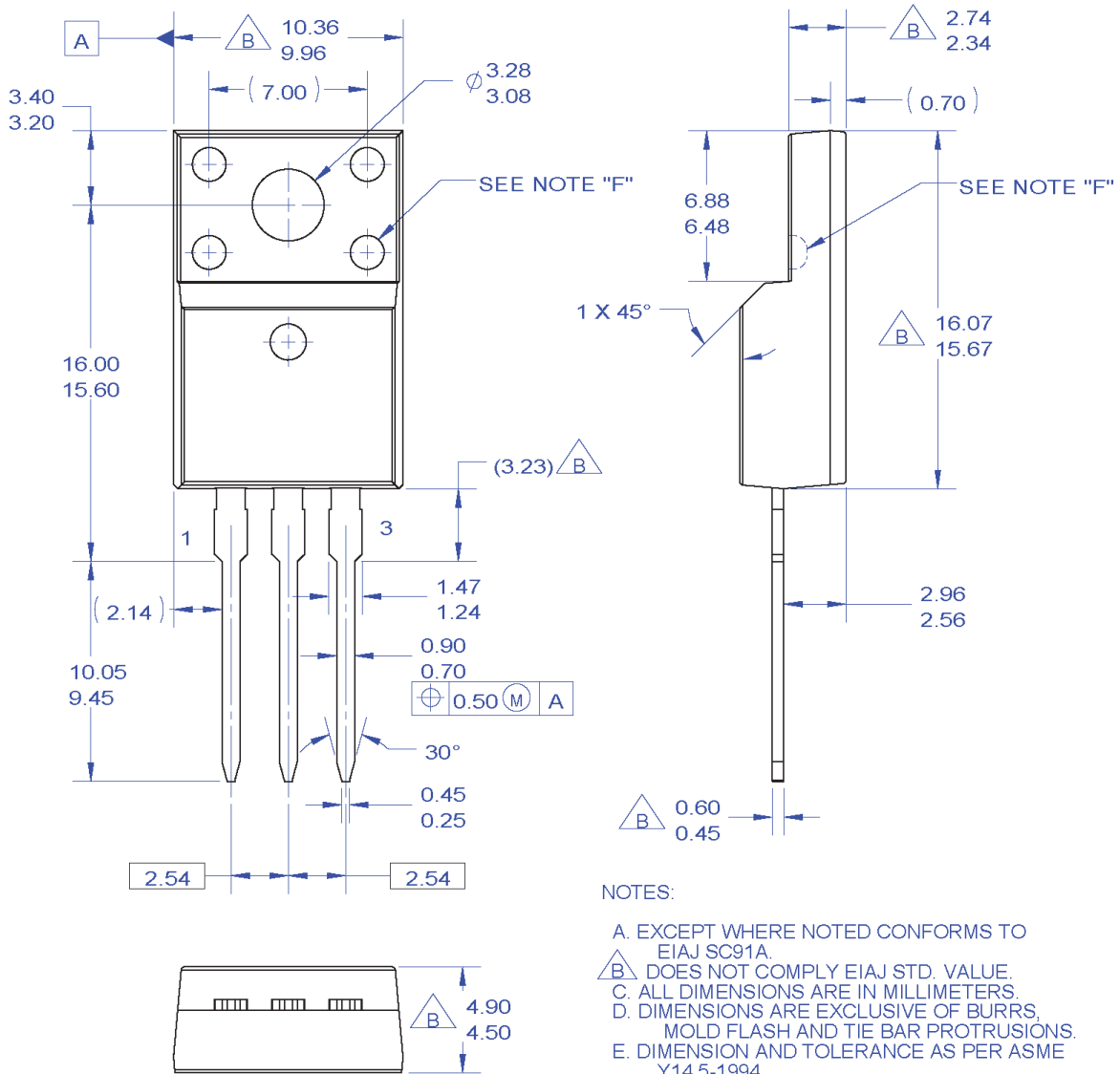


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3

Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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